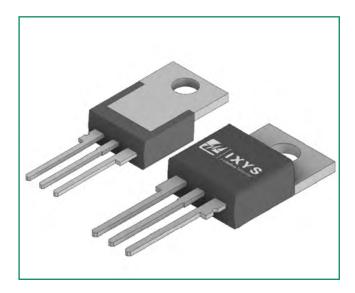
# MAC16HCDG, MAC16HCMG, MAC16HCNG

TRIAC - 400V - 800V







# **Description**

Designed primarily for full-wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full—wave, silicon gate—controlled devices are needed.

## **Features**

- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS at 80°C
- High Surge Current Capability150 Amperes
- Industry Standard TO-220 Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- These Devices are Pb-Free and are RoHS Compliant

# **Additional Information**







Accessories

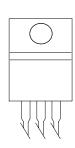


Samples

## **Functional Diagram**

#### Pin Out







## Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (- 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	V <sub>DRM</sub> , V <sub>RRM</sub>	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 8$	I <sub>T (RMS)</sub>	16	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 125°C)	I <sub>TSM</sub>	150	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	93	A²sec
Peak Gate Power ( $T_c = 80^{\circ}$ C, Pulse Width $\leq 1.0 \mu$ s)	$P_{GM}$	20	W
Average Gate Power (t = 8.3 ms, $T_c$ = 80°C)	$P_{G(AV)}$	0.5	W
Operating Junction Temperature Range	$T_{J}$	-40 to +125	°C
Storage Temperature Range	T <sub>stq</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>eJC</sub> R <sub>eJA</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		T <sub>L</sub>	260	°C

## Electrical Characteristics - OFF (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T_ = 25°C	I <sub>DRM</sub> ,	-	-	0.01	m Λ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	T <sub>J</sub> = 125°C	IRRM	-	_	2.0	mA

## Electrical Characteristics - ON (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic			Min	Тур	Max	Unit
Peak On-State Voltage (Note 2) ( $I_{TM} = \pm 21$ A Peak)		$V_{TM}$	_	-	1.6	V
Gate Trigger Current	MT2(+), G(+)		10	16	50	
(Continuous dc)	MT2(+), G(-)	I <sub>GT</sub>	10	18	50	mA
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)		10	22	50	
Gate Trigger Voltage	MT2(+), G(+)		0.5	8.0	1.5	
(Continuous dc)	MT2(+), G(-)	$V_{\rm GT}$	0.5	0.73	1.5	V
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)		0.5	0.82	1.5	
	MT2(+), G(+)		_	33	60	
Latching Current $(V_D = 24 \text{ V, } I_G = 50 \text{ mA})$	MT2(+), G(-)	$V_{GD}$	_	36	80	V
(v <sub>D</sub> = 2+ v, i <sub>G</sub> = 50 mm y	MT2(-), G(-)		-	33	50	
Holding Current ( $V_D = 12 V_{dc'}$ , Gate Open, Initiating Current = ±150 mA))		I <sub>H</sub>	-	20	50	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.



<sup>1.</sup> V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

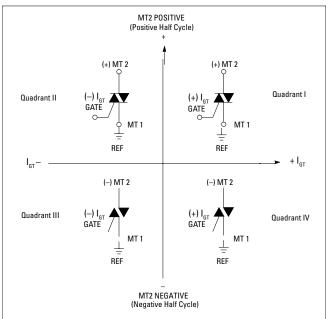
# **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current ( $V_D = 400 \text{ V}$ , $I_{TM} = 6.0 \text{ A}$ , Commutating dV/dt = 20 V/ $\mu$ s, Gate Open, $I_J = 125^{\circ}$ C, $I_{TM} = 10 \text{ M}$ , $I_{TM} = 10 \text{ M}$ , $I_{TM} = 10 \text{ M}$ , with Snubber)	(di/dt)c	15.0	_	-	A/ms
Critical Rate of Rise of Off-State Voltage $(V_D = Rated V_{DRM'}, Exponential Waveform, Gate Open, T_J = 125°C)$	dv/dt	750	_	_	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 200 mA/µsec; f = 60 Hz	di/dt	_	-	10	A/µs

# **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{_{RRM}}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
I <sub>H</sub>	Holding Current

## **Quadrant Definitions for a Triac**



All polarities are referenced to MT1. With in-phase signals (using standard AC lines) quadrants I and III are used.

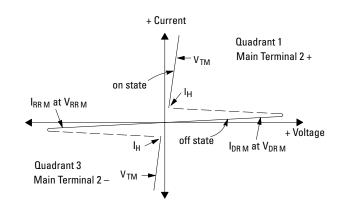


Figure 1. Typical Gate Trigger Current vs Junction Temperature

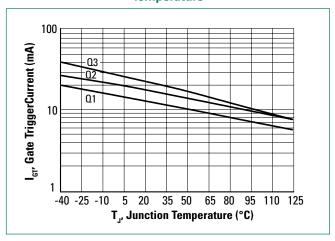
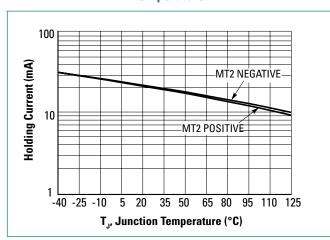


Figure 3. Typical Holding Current vs Junction Temperature



**Figure 5. Typical RMS Current Derating** 

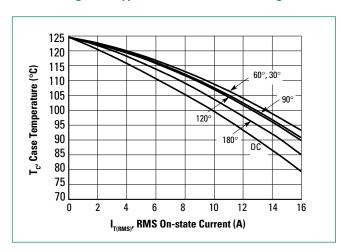


Figure 2. Typical Gate Trigger Voltage vs Junction Temperature

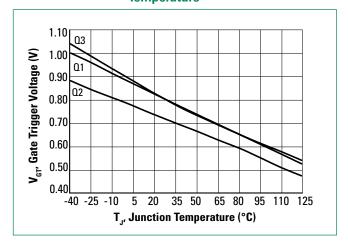


Figure 4. Typical Latching Current vs Junction Temperature

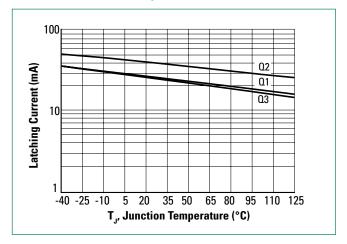
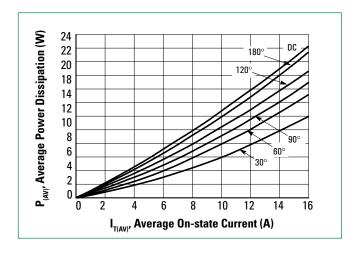


Figure 6. On-State Power Dissipation





**Figure 7. Typical On-State Characteristics** 

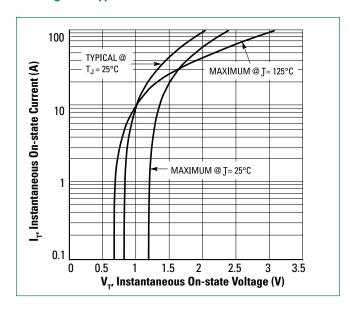
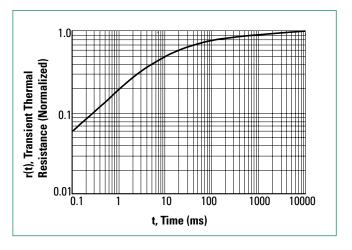
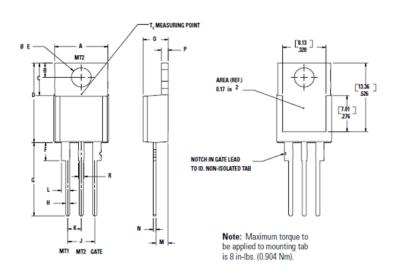


Figure 8. Typical Thermal Response

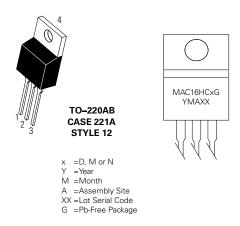




# **Dimensions**



## **Part Marking System**



ъ.	Millimeters Dim		Inches		
Dim	Min	Max	Min	Max	
Α	0.380	0.420	9.65	10.67	
В	0.105	0.115	2.67	2.92	
С	0.230	0.250	5.84	6.35	
D	0.590	0.620	14.99	15.75	
E	0.142	0.147	3.61	3.73	
F	0.110	0.130	2.79	3.30	
G	0.540	0.575	13.72	14.61	
Н	0.025	0.035	0.64	0.89	
J	0.195	0.205	4.95	5.21	
K	0.095	0.105	2.41	2.67	
L	0.060	0.075	1.52	1.91	
M	0.085	0.095	2.16	2.41	
N	0.018	0.024	0.46	0.61	
0	0.178	0.188	4.52	4.78	
P	0.045	0.060	1.14	1.52	
R	0.038	0.048	0.97	1.22	

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	Main Terminal 2			

## **Ordering Information**

Device	Package	Shipping
MAC16HCDG	TO 222	
MAC16HCMG	TO-220 (Pb-Free)	1000 Units/ Box
MAC16HCNG	(1.5.1100)	

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